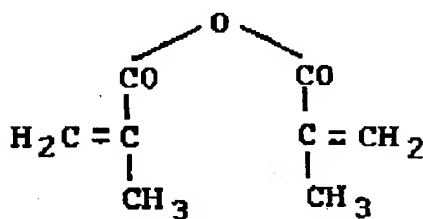


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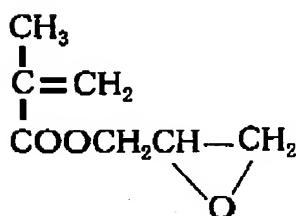
AMENDMENT TO THE SPECIFICATION

Please replace the paragraph bridging pages 17 and 18 with the following,  
wherein an attachment hereto is marked up to show the changes made to that paragraph:

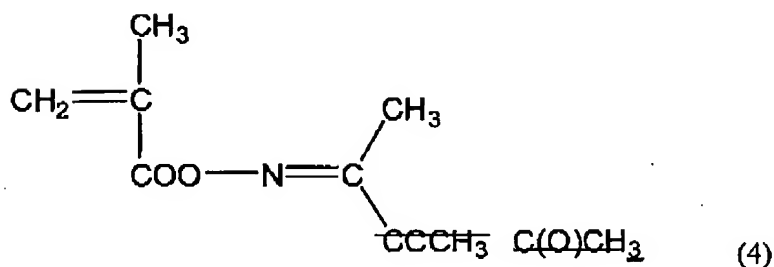
As a factor for expanding the sensitivity region, there can be selectively employed a structure having a function of expanding the photosensitive wavelength region, and there can be advantageously utilized a monomer unit obtained by copolymerizing a monomer capable of expanding the sensitivity region toward a longer wavelength side as represented by following formulas (2) to (6):



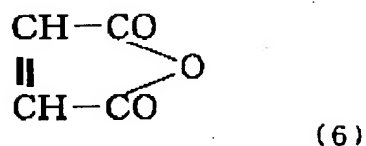
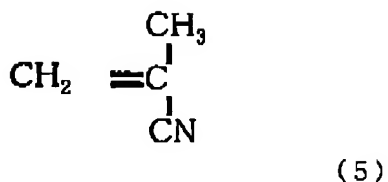
(2)



(3)



(4)



Please amend the paragraph appearing at Page 27, which includes lines 9 and 10 thereof, to read as follows:

Then, after the removal of the covering resin 7 by dissolution the mold pattern 3 is irradiated, as shown in Fig. 1E, by an ionizing radiation of a wavelength of 300 nm or less across the liquid flow path in structure member 4 constituted of a hardened portion by the pattern exposure to the negative-working photosensitive material layer. Such irradiation intends to decompose the crosslinked positive-working resist constituting the mode pattern 3 to a lower molecular weight, thereby enabling easy removal thereof.

Please replace the paragraph bridging pages 45 and 46 with the following, wherein an attachment hereto is marked up to show the changes made to that paragraph:

Then, on the rear surface of the processed substrate, an etching mask [[7]] having an aperture of a width of 1 mm and a length of 10 mm was prepared with a polyetheramide composition (HIMAL, manufactured by Hitachi Chemical Co.). Then the substrate was subjected to an anisotropic etching by immersion in a 22 wt.% TMAH aqueous solution maintained at 80°C, thereby forming an ink supply aperture 210. In this operation, in order to protect the [[ink]] water repellent layer 5 (which also repels ink) from the etching solution, the anisotropic etching was conducted after coating a protective film (OBC manufactured by Tokyo Oka Industries Co.; not shown) on the ink repellent layer.